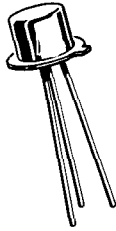


**2N2369A (SILICON)**  
**(JAN 2N2369A AVAILABLE)**

$V_{CE0} = 15 \text{ V}$   
 $t_{on} < 12 \text{ ns}$   
 $t_{off} < 18 \text{ ns}$



**CASE 22**  
(TO-18)

NPN silicon epitaxial transistor for high-speed range of .10 – 100 mA dc switching applications. Specifications provided at  $-55^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$  for critical dc characteristics.

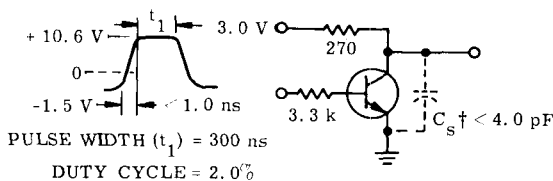
Collector connected to case

**MAXIMUM RATINGS**

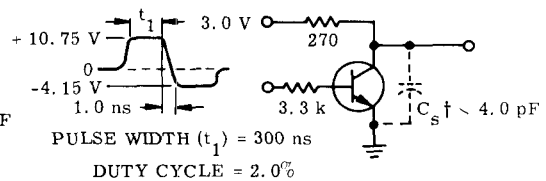
Rating	Symbol	Value	Unit
Collector-Emmitter Voltage	$V_{CE0}$	15	Vdc
Collector-Emmitter Voltage	$V_{CES}$	40	Vdc
Collector-Base Voltage	$V_{CB}$	40	Vdc
Emitter-Base Voltage	$V_{EB}$	4.5	Vdc
Collector Current – Continuous	$I_C$	200	mA dc
Peak (10 $\mu\text{s}$ Pulse)		500	
Total Device Dissipation @ $T_A = 25^{\circ}\text{C}$	$P_D$	0.36	Watt
Derate above $25^{\circ}\text{C}$		2.06	mW/ $^{\circ}\text{C}$
Total Device Dissipation @ $T_C = 25^{\circ}\text{C}$	$P_D$	1.2	Watts
Derate above $25^{\circ}\text{C}$		6.85	mW/ $^{\circ}\text{C}$
Operating Junction Temperature Range	$T_J$	+200	$^{\circ}\text{C}$
Storage Temperature Range	$T_{stg}$	-65 to +200	$^{\circ}\text{C}$

**SWITCHING TIME EQUIVALENT TEST CIRCUITS**

**FIGURE 1 –  $t_{on}$  CIRCUIT – 10 mA**



**FIGURE 2 –  $t_{off}$  CIRCUIT – 10 mA**



† Total shunt capacitance of test jig and connectors.